Daniel B Habersat

List of Publications by Citations

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43	1,125	16	33
papers	citations	h-index	g-index
44	**1,292**	**0.9**	**4.36**
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
43	Basic Mechanisms of Threshold-Voltage Instability and Implications for Reliability Testing of SiC MOSFETs. *IEEE Transactions on Electron Devices*, **2015**, 62, 316-323	2.9	225
42	Time Dependence of Bias-Stress-Induced SiC MOSFET Threshold-Voltage Instability Measurements. *IEEE Transactions on Electron Devices*, **2008**, 55, 1835-1840	2.9	205
41	A Physical Model of High Temperature 4H-SiC MOSFETs. *IEEE Transactions on Electron Devices*, **2008**, 55, 2029-2040	2.9	109
40	Characterization of Transient Gate Oxide Trapping in SiC MOSFETs Using Fast $I$$V$ Techniques. *IEEE Transactions on Electron Devices*, **2008**, 55, 2004-2012	2.9	94
39	Application of reliability test standards to SiC Power MOSFETs **2011**,		46
38	Bias Stress-Induced Threshold-Voltage Instability of SiC MOSFETs. *Materials Science Forum*, **2006**, 527-529, 1317-1320	0.4	39
37	Threshold-voltage bias-temperature instability in commercially-available SiC MOSFETs. *Japanese Journal of Applied Physics*, **2016**, 55, 04EA03	1.4	37
36	High-Temperature Reliability of SiC Power MOSFETs. *Materials Science Forum*, **2011**, 679-680, 599-602	0.4	36
35	Two-Way Tunneling Model of Oxide Trap Charging and Discharging in SiC MOSFETs. *Materials Science Forum*, **2012**, 717-720, 465-468	0.4	32
34	Temperature-Dependence of SiC MOSFET Threshold-Voltage Instability. *Materials Science Forum*, **2008**, 600-603, 807-810	0.4	32
33	SiC MOSFET threshold-stability issues. *Materials Science in Semiconductor Processing*, **2018**, 78, 32-37	4.3	26
32	Measurement considerations for evaluating BTI effects in SiC MOSFETs. *Microelectronics Reliability*, **2018**, 81, 121-126	1.2	21
31	Advances in pulsed-laser-deposited AlN thin films for high-temperature capping, device passivation, and piezoelectric-based RF MEMS/NEMS resonator applications. *Journal of Electronic Materials*, **2006**, 35, 777-794	1.9	18
30	The Effect of Nitridation on SiC MOS Oxides as Evaluated by Charge Pumping. *Materials Science Forum*, **2008**, 600-603, 743-746	0.4	17
29	(Invited) Effect of Threshold-Voltage Instability on SiC Power MOSFET High-Temperature Reliability. *ECS Transactions*, **2011**, 41, 203-214	1	16
28	Time-Dependent Bias Stress-Induced Instability of SiC MOS Devices. *Materials Research Society Symposia Proceedings*, **2006**, 911, 5		16
27	Comparison of Test Methods for Proper Characterization of VT in SiC MOSFETs. *Materials Science Forum*, **2016**, 858, 833-839	0.4	14

26	Evaluations of threshold voltage stability on COTS SiC DMOSFETs using fast measurements **2016**,		14
25	Evaluation of PBTS and NBTS in SiC MOS Using In Situ Charge Pumping Measurements. *Materials Science Forum*, **2013**, 740-742, 545-548	0.4	12
24	A Study of High Temperature DC and AC Gate Stressing on the Performance and Reliability of Power SiC MOSFETs. *Materials Science Forum*, **2013**, 740-742, 549-552	0.4	11
23	Charge Trapping in Sic Power MOSFETs and its Consequences for Robust Reliability Testing. *Materials Science Forum*, **2012**, 717-720, 1085-1088	0.4	11
22	Detection of Mobile Ions in the Presence of Charge Trapping in SiC MOS Devices. *Materials Science Forum*, **2012**, 717-720, 461-464	0.4	10
21	On Separating Oxide Charges and Interface Charges in 4H-SiC Metal-Oxide-Semiconductor Devices. *Materials Science Forum*, **2006**, 527-529, 1007-1010	0.4	10
20	Effect of ON-State Stress on SiC DMOSFET Subthreshold I-V Characteristics. *Materials Science Forum*, **2010**, 645-648, 983-986	0.4	9
19	Feasibility of SiC Threshold Voltage Drift Characterization for Reliability Assessment in Production Environments. *Materials Science Forum*, **2017**, 897, 509-512	0.4	8
18	Improved Observation of SiC/SiO2 Oxide Charge Traps Using MOS C-V. *Materials Science Forum*, **2011**, 679-680, 366-369	0.4	8
17	Temperature-dependent threshold stability of COTS SiC MOSFETs during gate switching **2017**,		7
16	Measurement Issues Affecting Threshold-Voltage Instability Characterization of SiC MOSFETs. *Materials Science Forum*, **2016**, 858, 461-464	0.4	6
15	Implications of Threshold-Voltage Instability on SiC DMOSFET Operation. *Materials Science Forum*, **2009**, 615-617, 809-812	0.4	6
14	Permanent and Transient Effects of High-Temperature Bias Stress on Room- Temperature V_{T} Drift Measurements in SiC Power MOSFETs **2019**,		4
13	Bias-Temperature-Stress Response of Commercially-Available SiC Power MOSFETs. *Materials Science Forum*, **2015**, 821-823, 677-680	0.4	4
12	Simulating ion transport and its effects in silicon carbide power MOSFET gate oxides **2013**,		3
11	Investigation of a high temperature oxide-trap activation model for SiC power MOSFETs **2011**,		3
10	Improvements in SiC MOS Processing as Revealed by Studies of Fixed and Oxide Trap Charge. *Materials Science Forum*, **2009**, 615-617, 769-772	0.4	3
9	Using a First Principles Coulomb Scattering Mobility Model for 4H-SiC MOSFET Device Simulation. *Materials Science Forum*, **2006**, 527-529, 1321-1324	0.4	3

8	Determination of the Temperature and Field Dependence of the Interface Conductivity Mobility in 4H-SiC/SiO2. *Materials Science Forum*, **2006**, 527-529, 1055-1058	0.4	2
7	Threshold-Voltage Instability in SiC MOSFETs Due to Near-Interfacial Oxide Traps. *Materials Science Forum*, **2016**, 858, 585-590	0.4	2
6	Influence of High-Temperature Bias Stress on Room-Temperature VT Drift Measurements in SiC Power MOSFETs. *Materials Science Forum*, **2019**, 963, 757-762	0.4	2
5	Influences of Bias Interruption and Reapplication on High-Temperature Threshold-Voltage Shifts of SiC DMOSFETs. *Materials Science Forum*, **2018**, 924, 743-747	0.4	2
4	Simulating the Influence of Mobile Ionic Oxide Charge on SiC MOS Bias-Temperature Instability Measurements. *Materials Science Forum*, **2015**, 821-823, 697-700	0.4	1
3	Towards a Robust Approach to Threshold Voltage Characterization and High Temperature Gate Bias Qualification **2020**,		1
2	(Invited) Implications for Robust Reliability Testing of Power SiC MOSFETs. *ECS Transactions*, **2011**, 41, 215-224	1	
1	Investigation of Drain Current Saturation in 4H-SiC MOSFETs. *Materials Science Forum*, **2007**, 556-557, 811-814	0.4	